

**9.17** Find  $f_T$  for a MOSFET operating at  $I_D = 100 \mu\text{A}$  and  $V_{OV} = 0.2 \text{ V}$ . The MOSFET has  $C_{gs} = 20 \text{ fF}$  and  $C_{gd} = 5 \text{ fF}$ .

**9.20** It is required to calculate the intrinsic gain  $A_0$  and the unity-gain frequency  $f_T$  of an  $n$ -channel transistor fabricated in a  $0.18\text{-}\mu\text{m}$  CMOS process for which  $L_{ov} = 0.1 L_t$ ,  $\mu_n = 450 \text{ cm}^2/\text{V}\cdot\text{s}$ , and  $V'_A = 5 \text{ V}/\mu\text{m}$ . The device is operated at  $V_{OV} = 0.2 \text{ V}$ . Find  $A_0$  and  $f_T$  for devices with  $L = L_{\min}$ ,  $2L_{\min}$ ,  $3L_{\min}$ ,  $4L_{\min}$ , and  $5L_{\min}$ . Present your results in a table.

**9.29** In a particular common-source amplifier for which the midband voltage gain between gate and drain (i.e.,  $-g_m R'_L$ ) is  $-29 \text{ V/V}$ , the NMOS transistor has  $C_{gs} = 0.5 \text{ pF}$  and  $C_{gd} = 0.1 \text{ pF}$ . What input capacitance would you expect? For what range of signal-source resistances can you expect the 3-dB frequency to exceed  $10 \text{ MHz}$ ? Neglect the effect of  $R_G$ . (see Fig. 9.2(a))

**9.33** A discrete MOSFET common-source amplifier has  $R_G = 1 \text{ M}\Omega$ ,  $g_m = 5 \text{ mA/V}$ ,  $r_o = 100 \text{ k}\Omega$ ,  $R_D = 10 \text{ k}\Omega$ ,  $C_{gs} = 2 \text{ pF}$ , and  $C_{gd} = 0.4 \text{ pF}$ . The amplifier is fed from a voltage source with an internal resistance of  $500 \text{ k}\Omega$  and is connected to a  $10\text{-k}\Omega$  load. Find:

- (a) the overall midband gain  $A_M$  (see Fig. 9.2(a))
- (b) the upper 3-dB frequency  $f_H$

Ignore pole at output node

**9.35** The NMOS transistor in the discrete CS amplifier circuit of Fig. P9.3 is biased to have  $g_m = 1 \text{ mA/V}$  and  $r_o = 100 \text{ k}\Omega$ . Find  $A_M$ . If  $C_{gs} = 1 \text{ pF}$  and  $C_{gd} = 0.2 \text{ pF}$ , find  $f_H$ .

**9.44** An amplifier with a dc gain of  $60 \text{ dB}$  has a single-pole high-frequency response with a 3-dB frequency of  $10 \text{ kHz}$ .

- (a) Give an expression for the gain function  $A(s)$ .
- (b) Sketch Bode diagrams for the gain magnitude and phase.
- (c) What is the gain-bandwidth product?
- (d) What is the unity-gain frequency?

**9.57** An ideal voltage amplifier with a voltage gain of  $-1000 \text{ V/V}$  has a  $0.2\text{-pF}$  capacitance connected between its output and input terminals. What is the input capacitance of the amplifier? If the amplifier is fed from a voltage source  $V_{\text{sig}}$  having a resistance  $R_{\text{sig}} = 1 \text{ k}\Omega$ , find the transfer function  $V_o/V_{\text{sig}}$  as a function of the complex-frequency variable  $s$  and hence the 3-dB frequency  $f_H$  and the unity-gain frequency  $f_T$ .

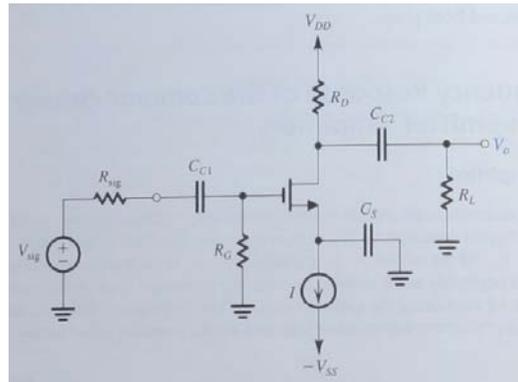


Fig. 9.2(a)

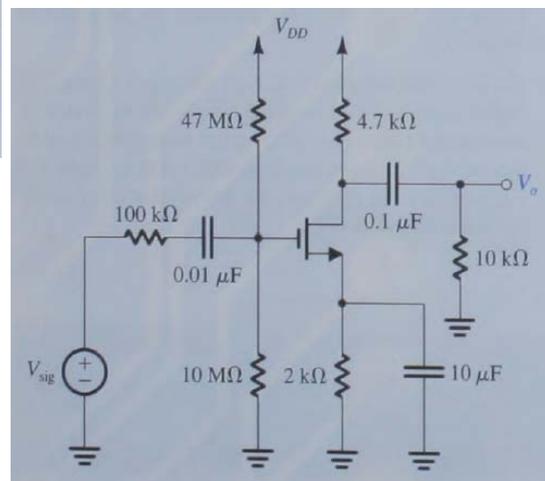


Fig. P9.3

**9.60** A CS amplifier that can be represented by the equivalent circuit of Fig. 9.19 has  $C_{gs} = 2$  pF,  $C_{gd} = 0.1$  pF,  $C_L = 2$  pF,  $g_m = 4$  mA/V, and  $R'_{sig} = R'_L = 20$  k $\Omega$ . Find

the midband gain,  $A_M$

Use Millers Theorem and then find the estimated pole locations at the input and output nodes.

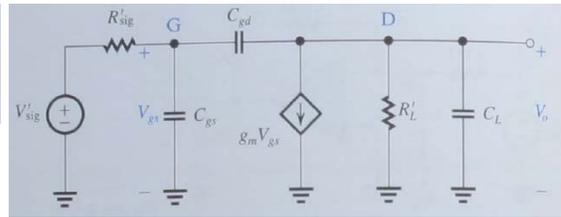


Fig. 9.19

**9.79** Find the dc gain and the 3-dB frequency of a MOS cascode amplifier operated at  $g_m = 1$  mA/V and  $r_o = 50$  k $\Omega$ . The MOSFETs have  $C_{gs} = 30$  fF,  $C_{gd} = 10$  fF, and  $C_{db} = 10$  fF. The amplifier is fed from a signal source with  $R_{sig} = 100$  k $\Omega$  and is connected to a load resistance of 2 M $\Omega$ . There is also a load capacitance  $C_L$  of 40 fF.

Use OTC method for finding  $f_H$

**9.85** A source follower has  $g_m = 5$  mA/V,  $r_o = 20$  k $\Omega$ ,  $R_{sig} = 20$  k $\Omega$ ,  $R_L = 2$  k $\Omega$ ,  $C_{gs} = 2$  pF,  $C_{gd} = 0.1$  pF, and  $C_L = 1$  pF. Find  $A_{vs}$ ,  $R_{o1}$ , and  $f_H$

Use OTC method for finding  $f_H$